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Infrared Applications of Semiconductors II

Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Table of Contents

[More information](#)

CONTENTS

Preface	xv
---------------	----

Acknowledgments	xvii
-----------------------	------

Materials Research Society Symposium Proceedings	xviii
--	-------

**PART I: ANTIMONIDE RELATED MATERIALS - GROWTH,
CHARACTERIZATION, AND ANALYSIS**

* Materials for Mid-IR Semiconductor Lasers	3
<i>A.R. Kost</i>	
The Growth of Type-II IR Laser Structures	11
<i>M.J. Yang, W.J. Moore, B.R. Bennett, B.V. Shanabrook, and J.O. Cross</i>	
Nondestructive and Whole Wafer Characterization of III-V IR Epitaxial Materials Prepared by Turbo Disk Metalorganic Chemical Vapor Deposition	13
<i>Z.C. Feng, M. Pelczynski, C. Beckham, P. Cooke, I. Ferguson, and R.A. Stall</i>	
*Recent Progress in the Growth of Mid-IR Emitters by Metalorganic Chemical Vapor Deposition	19
<i>R.M. Biefeld, A.A. Allerman, S.R. Kurtz, and K.C. Baucom</i>	
TEM Investigation of $\text{Al}_{0.5}\text{Ga}_{0.5}\text{As}_{1-y}\text{Sb}_y$ Buffer-Layer Systems	31
<i>E. Chen, J.S. Ahearn, K. Nichols, P. Uppal, and D.C. Paine</i>	
Substrate Misorientation Effects on Epitaxial GaInAsSb .	37
<i>C.A. Wang, H.K. Choi, D.C. Oakley, and G.W. Charache</i>	
Bridgman Growth and Characterization of Bulk Single Crystals of $\text{Ga}_{1-x}\text{In}_x\text{Sb}$ for Thermophotovoltaic Applications	45
<i>J.R. Boyer and W.T. Haines</i>	
Photoreflectance Study of MBE-Grown Te-Doped GaSb at the $E_0 + \Delta_0$ Transition	57
<i>S. Iyer, S. Mulugeta, J. Li, B. Mangalam, S. Venkatraman, and K.K. Bajaj</i>	
Surface and Interface Properties of InSb Epitaxial Thin Films Grown on GaAs by Low-Pressure Metalorganic Chemical Vapor Deposition	63
<i>K. Li, K.L. Tan, M. Pelczynski, Z.C. Feng, A.T.S. Wee, J.Y. Lin, I. Ferguson, and R.A. Stall</i>	

*Invited Paper

PART II: ANTIMONIDE RELATED DEVICES

*Theoretical Performance of Mid-ir Broken-Gap Multilayer Superlattice Lasers	71
<i>Michael E. Flatté, J.T. Olesberg, and C.H. Grein</i>	
Auger Recombination in Antimony-Based, Strain-Balanced, Narrow-Bandgap Superlattices	83
<i>J.T. Olesberg, Thomas F. Boggess, S.A. Anson, D.J. Jang, M.E. Flatté, T.C. Hasenberg, and C.H. Grein</i>	
High-Power Mid-IR Interband Cascade Lasers	89
<i>B.H. Yang, D. Zhang, Rui Q. Yang, C.H. Lin, S.J. Murry, H. Wu, and S.S. Pei</i>	
Mid-IR Vertical-Cavity Surface-Emitting Lasers	95
<i>I. Vurgaftman, W.W. Bewley, C.L. Felix, E.H. Aifer, J.R. Meyer, L. Goldberg, D.H. Chow, and E. Selvig</i>	
3.2 and 3.8 μm Emission and Lasing in AlGaAsSb/InGaAsSb Double Heterostructures With Asymmetric Band Offset Confinements	101
<i>M.P. Mikhallova, B.E. Zhurtanov, K.D. Moiseev, A.N. Imenkov, O.G. Ershov, and Yu.P. Yakovlev</i>	
*High-Power, Low-Threshold, Optically Pumped Type-II Quantum-Well Lasers	107
<i>Chih-Hsiang Lin, S.J. Murry, Rui Q. Yang, S.S. Pei, H.Q. Le, Chi Yan, D.M. Gianardi, Jr., D.L. McDaniel, Jr., and M. Falcon</i>	
Modeling of Mid-IR Multiquantum-Well Lasers	117
<i>A.D. Andreev</i>	
Tunneling Effects in InAs/GaInSb Superlattice IR Photodiodes	123
<i>U. Weimar, F. Fuchs, E. Ahlswede, J. Schmitz, W. Pletschen, N. Herres, and M. Walther</i>	
Mid-IR Photodetectors Based on InAs/InGaSb Type-II Quantum Wells	129
<i>G.J. Brown, M. Ahoujja, F. Szmulowicz, W.C. Mitchel, and C.H. Lin</i>	
Progress on GaInAsSb and InAsSbP Photodetectors for Mid-IR Wavelengths	135
<i>Z.A. Shellenbarger, M.G. Mauk, P.E. Sims, J.A. Cox, J.D. Lesko, J.R. Bower, J.D. South, and L.C. Dinetta</i>	

PART III: INNOVATIVE IR DEVICES

*Nonequilibrium InSb/InAlSb Diodes Grown by MBE	143
<i>A.D. Johnson, A.B.J. Smout, J.W. Cairns, G.J. Pryce, A.J. Piddock, R. Jefferies, T. Ashley, and C.T. Elliott</i>	
*Positive and Negative Luminescent IR Sources and Their Applications	153
<i>T. Ashley</i>	

*Invited Paper

GaAs/AIGaAs Intersubband Mid-IR Emitter 165

*G. Strasser, S. Gianordoli, L. Hvozdara, H. Bichl, K. Unterrainer,
E. Gornik, P. Kruck, M. Helm, and J.N. Heyman*

Novel Piezoelectric Heterostructure for All-Optical IR Light Modulation 171

V. Ortiz, N.T. Pelekanos, and Guido Mula

Multivalent Acceptor-Doped Germanium Lasers: A Solid-State Tunable Source From 75 to 300 μ m 177

*D.R. Chamberlin, O.D. Dubon, E. Bründermann, E.E. Haller,
L.A. Reichertz, G. Sirmain, A.M. Linhart, and H.P. Röser*

Band-Reject IR Metallic Photonic Bandgap Filters on Flexible Polyimide Substrate 183

Sandhya Gupta, Gary Tuttle, Mihail Sigalas, and Kai-Ming Ho

PART IV: IR DETECTORS***High-Temperature IR Photon Detector Performance 191**

C.H. Grein and H. Ehrenreich

Free Carrier Absorption in *p*-Type Epitaxial Si and GaAs Films for Far-IR Detection 199

A.G.U. Perera, W.Z. Shen, M.O. Tanner, K.L. Wang, and W. Schaff

Monolithically Integrated Dual-Band Quantum-Well IR Photodetector 205

*D.K. Sengupta, S.D. Gunapala, S.V. Bandara, F. Pool, J.K. Liu,
M. McKelvey, E. Luong, J. Torezan, J. Mumulo, W. Hong, J. Gill,
G.E. Stillman, A.P. Curtis, S. Kim, L.J. Chou, P.J. Mares, M. Feng,
K.C. Hsieh, S.L. Chuang, S.G. Bishop, Y.C. Chang, H.C. Liu, and W.I. Wang*

Germanium Far-IR Blocked Impurity Band Detectors 215

C.S. Olsen, J.W. Beeman, W.L. Hansen, and E.E. Haller

HgCdTe—An Unexpectedly Good Choice for (Near) Room-Temperature Focal Plane Arrays 221

W.E. Tennant and C. Cabelli

Bandgap Engineering of HgCdTe for Two-Color IR Detector Arrays by MOVPE 233

P. Mitra, F.C. Case, S.L. Barnes, M.B. Reine, P. O'Dette, and S.P. Tobin

Influence of Structural Defects and Zinc Composition Variation on the Device Response of Cd_{1-x}Zn_xTe Radiation Detectors 241

*H. Yoon, J.M. Van Scyoc, T.S. Gilbert, M.S. Goorsky, B.A. Brunett,
J.C. Lund, H. Hermon, M. Schieber, and R.B. James*

Analysis of Grain Boundaries, Twin Boundaries, and Te Precipitates in Cd_{1-x}Zn_xTe Grown by High-Pressure Bridgman Method 247

J.R. Heffelfinger, D.L. Medlin, and R.B. James

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Table of Contents

[More information](#)

Mapping of Large-Area Cadmium Zinc Telluride (CZT) Wafers: Apparatus and Methods	253
<i>B.A. Brunett, J.M. Van Scyoc, H. Yoon, T.S. Gilbert, T.E. Schlesinger, J.C. Lund, and R.B. James</i>	
Recent Improvements in Dry Etching of $Hg_{1-x} Cd_x Te$ by CH_4- Based Electron-Cyclotron-Resonance Plasmas	259
<i>M. Seelmann-Eggebert, A. Rar, H. Zimmermann, and P. Meisen</i>	
*Modular 64×64 CdZnTe Arrays With Multiplexer Readout for High-Resolution Nuclear Medicine Imaging	267
<i>J.M. Woolfenden, H.B. Barber, H.H. Barrett, E.L. Dereniak, J.D. Eskin, D.G. Marks, K.J. Matherson, E.T. Young, and F.L. Augustine</i>	
*Performance of p-i-n CdZnTe Radiation Detectors and Their Unique Advantages	273
<i>R. Sudharsanan, C.C. Stenstrom, P. Bennett, and G.D. Vakerlis</i>	
Fabrication of CdZnTe Strip Detectors for Large-Area Arrays	285
<i>C.M. Stahle, Z.Q. Shi, K. Hu, S.D. Barthelmy, S.J. Snodgrass, S.J. Lehtonen, K.J. Mach, L. Barbier, N. Gehrels, J.F. Krizmanic, D. Palmer, A.M. Parsons, and P. Shu</i>	
Mapping Detector Response Over the Area of a CdZnTe- Multiple-Electrode Detector	291
<i>C.L. Lingren, B. Apotovsky, J.F. Butler, F.P. Doty, S.J. Friesenhahn, A. Oganesyan, B. Pi, and S. Zhao</i>	
New Type of IR Photodetectors Based on Lead Telluride and Related Alloys	295
<i>D.R. Khokhlov</i>	
PbTe(Ga) - New Multispectral IR Photodetector	301
<i>A.I. Belogorokhov, I.I. Ivanchik, and D.R. Khokhlov</i>	
 PART V: GROWTH AND DOPING OF II-VI MATERIALS	
*Current Issues of High-Pressure Bridgman Growth of Semi-Insulating CdZnTe	309
<i>Csaba Szeles and Elgin E. Eissler</i>	
Improved CdZnTe Detectors Grown by Vertical Bridgman Process	319
<i>K.G. Lynn, M. Weber, H.L. Glass, J.P. Flint, and Cs. Szeles</i>	
The Reduction of the Defect Density in CdTe Buffer Layers for the Growth of HgCdTe ir Photodiodes on Si(211) Substrates	329
<i>H-Y. Wei, L. Salamanca-Riba, and N.K. Dhar</i>	
Control of Defects and Impurities in Production of CdZnTe Crystals by the Bridgman Method	335
<i>H.L. Glass, A.J. Socha, D.W. Bakken, V.M. Speziale, and J.P. Flint</i>	

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Table of Contents

[More information](#)

Dopants in HgCdTe	341
<i>M.A. Berding and A. Sher</i>	
Study on Deep-Level Traps in <i>p</i>-HgCdTe With DLTS	347
<i>S. Kawata, I. Sugiyama, N. Kajihara, and Y. Miyamoto</i>	
Reactive Ion Etching (RIE)-Induced <i>p</i>- to <i>n</i>-Type Conversion in Extrinsicallly-Doped <i>p</i>-Type HgCdTe	353
<i>C.A. Musca, E.P.G. Smith, J.F. Siliquini, J.M. Dell, J. Antoszewski, J. Piotrowski, and L. Faraone</i>	
DX-Like Centers and Photoconductivity Kinetics in PbTe-Based Alloys	359
<i>B.A. Akimov, V.A. Bogoyavlenskiy, V.N. Vasil'kov, and L.I. Ryabova</i>	
Raman and Photoluminescence Studies on Intrinsic and Cr-Doped ZnSe Single Crystals	365
<i>Brajesh K. Rai, S. Bhaskar, H.D. Bist, R.S. Katiyar, K-T. Chen, and A. Burger</i>	
Growth and Characterization of PbSe and Pb_{1-x}Sn_xSe Layers on Si(100)	371
<i>H.K. Sachar, I. Chao, X.M. Fang, and P.J. McCann</i>	
In Situ Spectroscopic Ellipsometry for Real-Time Composition Control of Hg_{1-x}Cd_xTe Grown by Molecular-Beam Epitaxy	377
<i>R. Dat, F. Aqariden, W.M. Duncan, D. Chandra, and H.D. Shih</i>	
Nonmonotonous Behavior of Temperature Dependence of Plasma Frequency and Effect of a Local Instability of the PbTe:In,Ga Lattice	383
<i>A.I. Belogorokhov, L.I. Belogorokhova, and D.R. Khokhlov</i>	
X-ray Characterization of PbTe/SnTe Superlattices	389
<i>S.O. Ferreira, E. Abramof, P.H.O. Kappl, A.Y. Ueta, H. Closs, C. Boschetti, P. Motisuke, and I.N. Bandeira</i>	
PART VI: INTERDIFFUSION IN QUANTUM-WELL MATERIALS AND IR APPLICATIONS	
*Quantum-Well Intermixing for Optoelectronic Applications	397
<i>C. Jagadish, H.H. Tan, S. Yuan, and M. Gal</i>	
The Effect of Tensile Strain on AlGaAs/GaAsP Interdiffused Quantum-Well Laser	413
<i>K.S. Chan and Michael C.Y. Chan</i>	
Reduced Al-Ga Interdiffusion in GaAs/AlGaAs Multiple-Quantum-Well Structure by Introducing Low Hydrogen Content SiN_x Capping Layer for Dielectric Cap Quantum-Well Disordering	419
<i>W.J. Choi, S.M. Han, S.I. Shah, S.G. Choi, D.H. Woo, S. Lee, H.J. Kim, I.K. Han, S.H. Kim, J.I. Lee, K.N. Kang, and J. Cho</i>	

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Table of Contents

[More information](#)

Theory of Critical Layer Thickness of Nonconstant Quantum-Well Width Produced by Interdiffusion and Its Optoelectronics Consequence	425
<i>Michael C.Y. Chan and E. Herbert Li</i>	
Active Antiguide Vertical-Cavity Surface-Emitting Lasers With Diffused Quantum-Well Structure	431
<i>S.F. Yu, E. Herbert Li, and W.M. Man</i>	
Modeling Interdiffusion in Superlattice Structures	437
<i>Richard G. Gass and Howard E. Jackson</i>	
Cation Interdiffusion in GaInP/GaAs Single Quantum Wells	441
<i>Joseph Micallef, Andrea Brincat, and Wai-Chee Shiu</i>	
Interdiffusion Mechanisms in GaAs/AlGaAs Quantum-Well Heterostructures Induced by SiO₂ Capping and Annealing	447
<i>A. Pépin, C. Vieu, M. Schneider, H. Launois, and E.V.K. Rao</i>	
Disorder-Delineated AlGaAs/GaAs Quantum-Well Phase Modulator	453
<i>W.C.H. Choy and B.L. Weiss</i>	
Thermal Interdiffusion in InGaAs/GaAs Strained Multiple-Quantum-Well IR Photodetector	459
<i>Alex S.W. Lee, E. Herbert Li, and Gamani Karunasiri</i>	
Analysis of AlGaAs/GaAs Multiple-Quantum-Well Dual Waveguides Defined by Ion Implantation-Induced Intermixing	467
<i>Kai-Ming Lo</i>	

PART VII: NONLINEAR OPTICAL AND OPO MATERIALS

*Second-Harmonic and Sum-Frequency Generation in CdGeAs₂	475
<i>Eiko Tanaka and Kiyoshi Kato</i>	
Low Optical Loss Wafer-Bonded GaAs Structures for Quasi-Phase-Matched Second-Harmonic Generation	481
<i>YewChung Sermon Wu, Robert S. Feigelson, Roger K. Route, Dong Zheng, Leslie A. Gordon, Martin M. Fejer, and Robert L. Byer</i>	
Phase-Matched Second-Harmonic Generation in Asymmetric Double Quantum Wells	487
<i>K.L. Vodopyanov, C.C. Phillips, I. Vurgaftman, and J.R. Meyer</i>	
Dark Soliton Formation for Light-Induced Waveguiding in Photorefractive InP:Fe	491
<i>M. Chauvet, S.A. Hawkins, G.J. Salamo, M. Segev, D.F. Bliss, and G. Bryant</i>	
*ZnGeP₂ and Its Relation to Other Defect Semiconductors	495
<i>A.W. Vere, L.L. Taylor, P.C. Smith, C.J. Flynn, M.K. Saker, and J. Jones</i>	
Growth of NLO Chalcopyrite Materials by OMVPE	507
<i>M.L. Timmons and K.J. Bachmann</i>	

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Editors: Donald L. McDaniel, M. Omar Manasreh, Richard H. Miles and Sivalingam Sivananthan

Table of Contents

[More information](#)

Laser Damage Studies of Silver Gallium Sulfide Single Crystals	519
<i>Warren Ruderman, John Maffetone, David E. Zelman, and Derrick M. Poirier</i>	
Atomistic Calculations of Dopant Binding Energies in ZnGeP₂	525
<i>Ravindra Pandey, Melvin C. Ohmer, A. Costales, and J.M. Recio</i>	
Photoresponse Studies of the Polarization Dependence of the CdGeAs₂ Band Edge	531
<i>G.J. Brown, M.C. Ohmer, and P.G. Schunemann</i>	
Refractive Index Measurements of Barium Titanate From .4 to 5.0 Microns and Implications for Periodically Poled Frequency Conversion Devices	537
<i>David E. Zelman, David L. Small, and Peter Schunemann</i>	
Polarized Raman Scattering Study of ZnGeP₂ Single Crystals	543
<i>Spirit Tlali, Howard E. Jackson, M.C. Ohmer, P.G. Schunemann, and T.M. Pollak</i>	
Electron-Nuclear Double Resonance Study of the Zinc Vacancy in Zinc Germanium Phosphide (ZnGeP₂)	549
<i>K.T. Stevens, S.D. Setzler, L.E. Halliburton, N.C. Fernelius, P.G. Schunemann, and T.M. Pollak</i>	
Influence of Quantum Confinement on the Photoemission From Nonlinear Optical Materials	555
<i>Kamakhya P. Ghatak, P.K. Bose, and Gautam Majumder</i>	
Extra-Wide Tuning Range Mid-IR Optical Parametric Generator Pumped by Er-Laser Pulses	561
<i>K.L. Vodopyanov</i>	
Operational Characteristics of GaSe Crystals for Mid-IR and Far-IR Applications	567
<i>N.C. Fernelius, F.K. Hopkins, N.B. Singh, D. Suhre, M. Marable, R.H. Hopkins, R. Meyer, and P. Mui</i>	
Frequency Doubling of cw and Pulsed CO₂ Lasers Using Diffusion-Bonded, Quasi-Phase-Matched GaAs Stacks	573
<i>Melvin C. Ohmer, Shekhar Guha, Ronald E. Perrin, Laura S. Rea, Phil Won Yu, and Ayub Fathimulla</i>	
Characterization of CdGeAs₂ Using Capacitance Methods	581
<i>S.R. Smith, A.O. Evvaraye, and M.C. Ohmer</i>	

PART VIII: RELATED CONTRIBUTIONS

Chemical Bonding on GaAs(001) Surfaces Passivated Using SeS₂	589
<i>Jingxi Sun, Dong Ju Seo, W.L. O'Brien, F.J. Himpsel, and T.F. Kuech</i>	
Er-Related Emission in Impurities (Nitrogen, Oxygen) Implanted Al_{0.7} Ga_{0.3} As	595
<i>S. Uekusa, M. Wakutani, M. Saito, and M. Kumagai</i>	

Photoacoustic Study of the Effect of 0.9 eV Light Illumination in Semi-Insulating GaAs	601
<i>Atsuhiko Fukuyama, Yoshito Akashi, Kenji Yoshino, Kouji Maeda, and Tetsuo Ikari</i>	
Photo-Assisted Resonant Tunneling Through Localized States in AlAs/GaAs Double-Barrier Structure With Undoped Spacer Layers	607
<i>H.Y. Chu, K-S. Lee, H-H. Park, and E-H. Lee</i>	
Oxygen-Related Defects in $In_{0.5}(Al_xGa_{1-x})_{0.5}$ P Grown by MOVPE	611
<i>J.G. Cederberg, B. Bieg, J-W. Huang, S.A. Stockman, M.J. Peanasky, and T.F. Kuech</i>	
Dislocations and Traps in MBE-Grown Lattice-Mismatched p-InGaAs/GaAs Layers on GaAs Substrates	617
<i>A.Y. Du, M.F. Li, T.C. Chong, and Z. Zhang</i>	
Study of the Homogeneity of Fe-Doped Semi-Insulating InP Wafers	625
<i>J. Jimenez, R. Formari, M. Curti, E. de la Puente, M. Avella, L.F. Sanz, M.A. Gonzalez, and A. Alvarez</i>	
Relaxed In_xGa_{1-x} As Graded Buffers Grown With Organometallic Vapor-Phase Epitaxy on GaAs	631
<i>M.T. Bulsara, C. Leitz, and E.A. Fitzgerald</i>	
γ-ray Irradiation Effect on the Intersubband Transition in InGaAs/AlGaAs Multiple Quantum Wells	637
<i>M.O. Manasreh, J.R. Chavez, W.T. Kemp, K. Hoenshel, and M. Missous</i>	
1.95 μm Compressively Strained InGaAs/InGaAsP Quantum- Well DFB Laser With Low Threshold	643
<i>Jie Dong, Akinori Ubukata, and Koh Matsumoto</i>	
Monolithic 1.55 μm Surface-Emitting Laser Structure With $In_{0.53}Al_{0.14}Ga_{0.33}$ As/$In_{0.52}Al_{0.48}$ As Distributed Bragg Reflector and Single Cavity Active Layer Grown by Metalorganic- Chemical-Vapor-Deposition Method	649
<i>J-H. Baek, B. Lee, W.S. Han, J.M. Smith, B.S. Jeong, and E-H. Lee</i>	
Effect of Geometric Factors on Polarization Properties of Vertical-Cavity Surface-Emitting Lasers With Tilted Pillar Structures	655
<i>Min Soo Park, Byung Tae Ahn, Hye Yong Chu, Byueng-Su Yoo, and Hyo-Hoon Park</i>	
High-Resolution X-ray Reflectometry and Diffraction of $CaF_2/Si(111)$ Structures Grown by Molecular-Beam Epitaxy	661
<i>E. Abramof, S.O. Ferreira, P.H.O. Rappi, A.Y. Ueta, C. Boschetti, H. Closs, P. Motisuke, and I.N. Bandeira</i>	
Optical Absorption in $Hg_{1-x}Cd_xTe$	667
<i>Vaidya Nathan</i>	

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Table of Contents

[More information](#)

The Burstein-Moss Shift in Quantum Dots of III-V, II-VI, and IV-VI Semiconductors Under Parallel Magnetic Field	673
<i>Kamakhy P. Ghatak, P.K. Bose, and Gautam Majumder</i>	
On the Moss-Burstein Shift in Quantum Confined Optoelectronic Ternary and Quaternary Materials	679
<i>Kamakhy P. Ghatak, P.K. Bose, and Gautam Majumder</i>	
Author Index	685
Subject Index	689